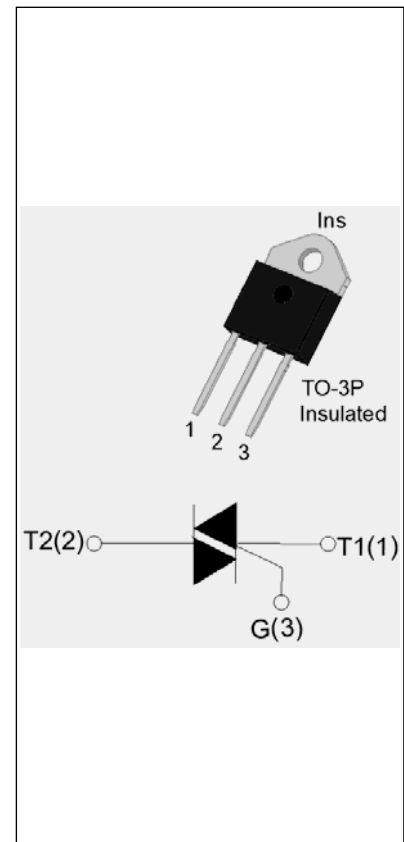


## DESCRIPTION:

The JST41Z-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST41Z-800BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST41Z-800BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.

## MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT} / /$	50/50/50	mA



## ABSOLUTE MAXIMUM RATINGS

Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-125	
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c = 81^\circ\text{C}$ )	$I_{T(RMS)}$	40	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	420	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		462	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	1000	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$di/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	8	A



Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	40	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1.5	kV

### ELECTRICAL CHARACTERISTICS ( $T_j=25$ unless otherwise specified)

$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	50	mA
$V_{GT}$		- -	MAX.	1.3	V
$V_{GD}$	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	80	mA
				200	
$I_H$	$I_T=500mA$		MAX.	100	mA
$dV/dt$	$V_D=540V$ Gate Open $T_j=125$		MIN.	2000	V/ $\mu s$
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s T_j=125$		MIN.	25	A/ms
$t_{on}$	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25$		TYP.	10	$\mu s$
$t_{off}$				70	

### STATIC CHARACTERISTICS

$V_{TM}$	$I_{TM}=60A t_p=380\mu s$	$T_j=25$	1.4	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.73	V
$R_D$	Dynamic resistance	$T_j=125$	10	m
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	$\mu A$
$I_{RRM}$		$T_j=125$	5	mA

### THERMAL RESISTANCES

$R_{th(j-c)}$	junction to case (AC)	0.85	/W
$R_{th(j-a)}$	junction to ambient (AC)	50	/W



## ORDERING INFORMATION

<b>J</b>	<b>ST</b>	<b>41</b>	<b>Z</b>	<b>-800</b>	<b>BW</b>
JieJie Microelectronics Co., Ltd.	Triacs IT(RMS):40A		Z:TO-3P(Ins)		BW:IGT1-3 50mA
				800:VDRM/VRRM 800V	

## MARKING

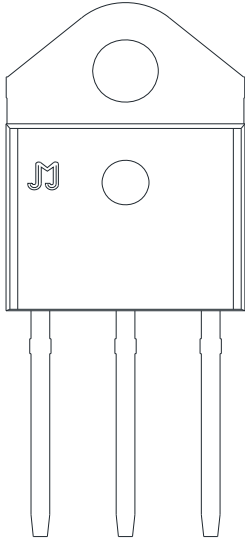

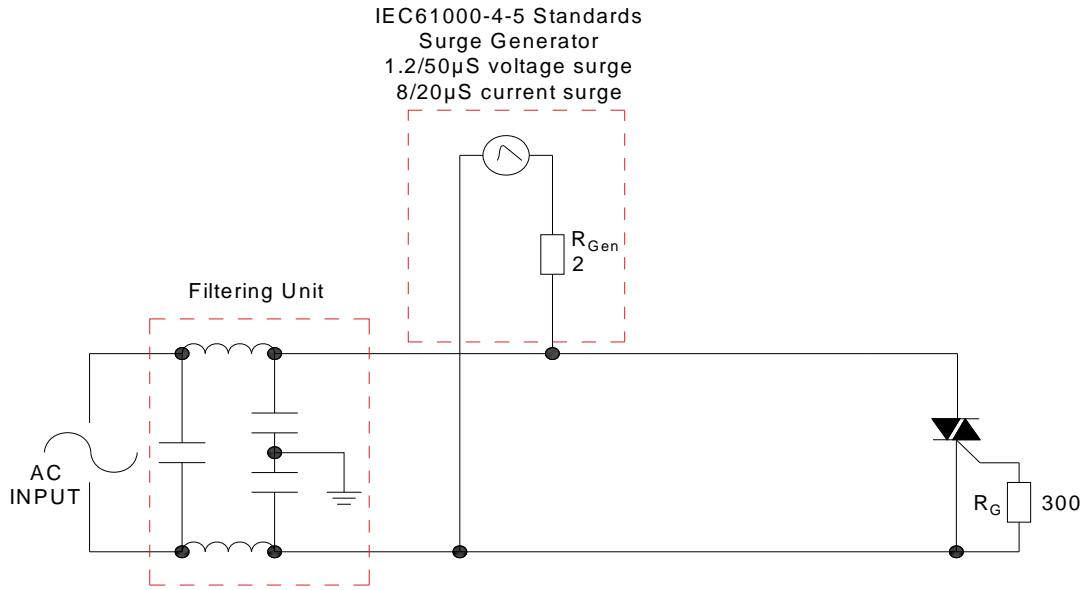
	
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FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

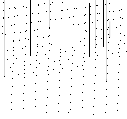
Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie





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## PACKAGE MECHANICAL DATA





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